



60V 175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BVDSS	R _{DS(ON)} max	I _D max T _C = +25°C
60V	11mΩ @ V _{GS} = 10V	47.6A
60 V	$16m\Omega @ V_{GS} = 4.5V$	39.5A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine management systems
- Body control electronics
- DC-DC converters

Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low Input Capacitance
- Fast Switching Speed
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DIODES™ DMTH6010LPDWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

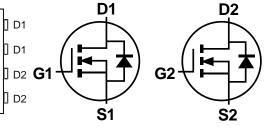
Mechanical Data

- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)

PowerDI5060-8/SWP (Type UXD)







Equivalent Circuit

Ordering Information (Note 4)

Part Number	Packago	Packing		
Part Number	Package	Qty.	Carrier	
DMTH6010LPDWQ-13	PowerDI5060-8/SWP (Type UXD)	2,500	Tape & Reel	

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

S1 l

S2 [

G2[

- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



⊃¦¦ = Manufacturer's Marking H6010LDW = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 22 = 2022) WW = Week (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	60	V	
Gate-Source Voltage		Vgss	±20	V
Continuous Drain Current (Note 6) $ T_C = +25^{\circ}C $ $T_C = +100^{\circ}C $		ID	47.6 33.7	А
Continuous Drain Current (Note 5) $ T_{A} = +25^{\circ}C $ $ T_{A} = +70^{\circ}C $		lo	13.1 10.9	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	90	А	
Maximum Continuous Body Diode Forward Current (Note 6)		Is	31	A
Avalanche Current, L = 0.1mH		las	20	A
Avalanche Energy, L = 0.1mH		Eas	20	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5) $T_A = +25^{\circ}C$		P_{D}	2.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Reja	53	°C/W	
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		PD	37.5	W
Thermal Resistance, Junction to Case (Note 6)	Rejc	4	°C/W	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

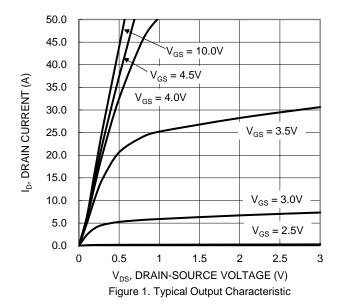
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	60	_	_	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μA	V _{DS} = 48V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(TH)	1	_	3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Danier	_	8.5	11	mΩ	V _G S = 10V, I _D = 20A	
Static Dialii-Source Off-Resistance	RDS(ON)	_	10.9	16	11122	$V_{GS} = 4.5V, I_D = 20A$	
Diode Forward Voltage	VsD	_	0.9	1.2	V	V _G S = 0V, I _S = 20A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		2615	_	pF		
Output Capacitance	Coss		1415	_	pF	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz	
Reverse Transfer Capacitance	Crss	_	58	_	pF	-11 = 11VIM2	
Gate Resistance	Rg	_	0.67	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	20.3	_	nC		
Total Gate Charge (V _{GS} = 10V)	Qg	_	40.2	_	nC	V 20V I 20A	
Gate-Source Charge	Qgs	_	5.9	_	nC	$V_{DS} = 30V, I_{D} = 20A$	
Gate-Drain Charge	Qgd	_	9.3	_	nC	1	
Turn-On Delay Time	tD(ON)	_	5.7	_	ns		
Turn-On Rise Time	t _R	_	8.8	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 20A, R_{G} = 3\Omega$	
Turn-Off Delay Time	tD(OFF)		20.8	_	ns		
Turn-Off Fall Time	tF		7.4	_	ns		
Body Diode Reverse Recovery Time	t _{RR}		34.5	_	ns	1 004 31/31 4004/5	
Body Diode Reverse Recovery Charge	Q _{RR}		37.5	_	nC	$I_F = 20A$, di/dt = 100A/ μ s	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

^{5.} Device involved on the state of the state of







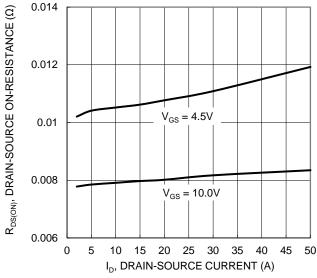


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

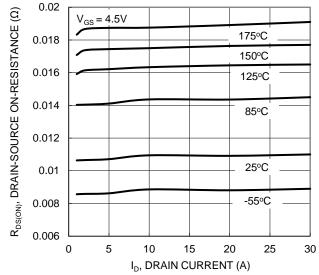
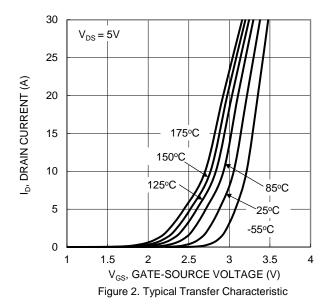
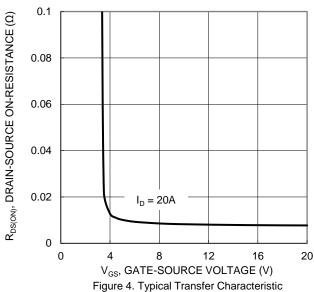


Figure 5. Typical On-Resistance vs Drain Current and Junction Temperature





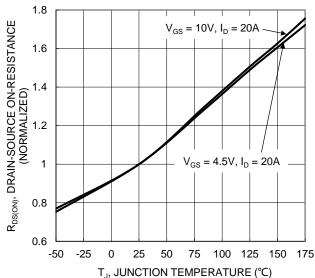


Figure 6. On-Resistance Variation with Junction Temperature





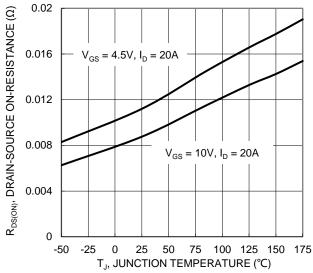
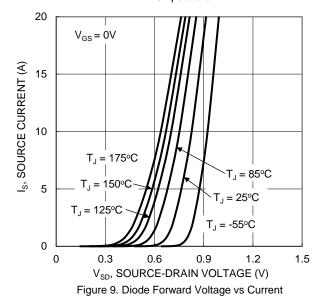


Figure 7. On-Resistance Variation with Junction Temperature



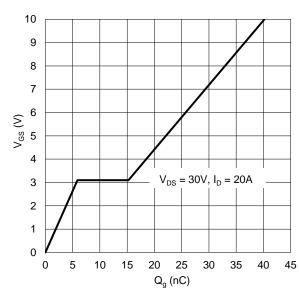


Figure 11. Gate Charge

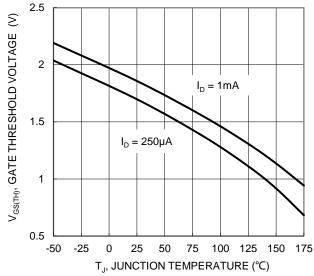


Figure 8. Gate Threshold Variation vs Junction Temperature

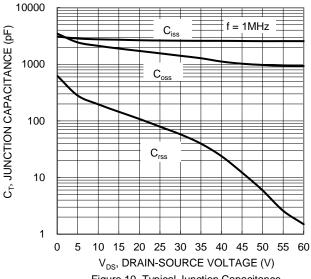
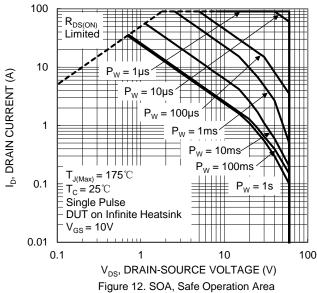


Figure 10. Typical Junction Capacitance





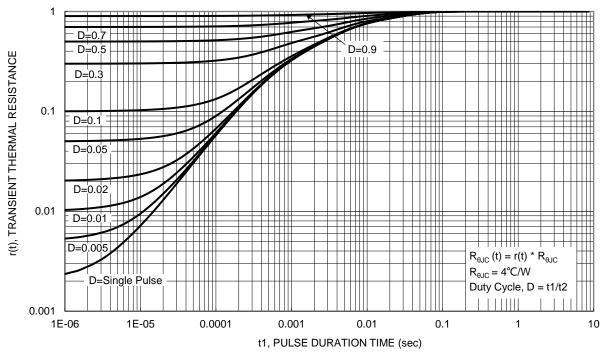


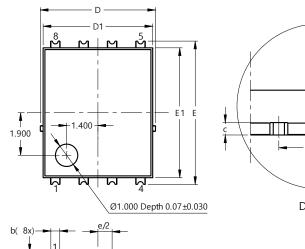
Figure 13. Transient Thermal Resistance

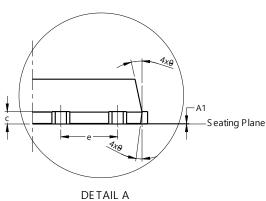


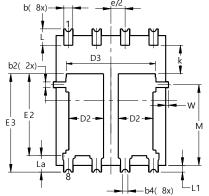
Package Outline Dimensions

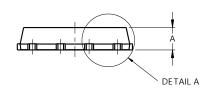
Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UXD)







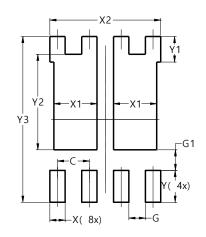


PowerDI5060-8/SWP (Type UXD)					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A 1	0.00	0.05			
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4	().25REF			
С	0.230	0.330	0.277		
D	5.15 BSC				
D1	4.70	5.10	4.90		
D2	1.46	1.66	1.55		
D3	3.78	4.18	3.98		
Е	6	.40 BS0			
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
E2a	4.195	4.595	4.395		
е	1	.27BSC			
k	1.05				
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
М	3.205	4.005	3.605		
W	0.025	0.225	0.125		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UXD)



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
X	0.610
X1	1.720
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610



IMPORTANT NOTICE

- 1. DIODES INCORPORATED (Diodes) AND ITS SUBSIDIARIES MAKE NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO ANY INFORMATION CONTAINED IN THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).
- 2. The Information contained herein is for informational purpose only and is provided only to illustrate the operation of Diodes' products described herein and application examples. Diodes does not assume any liability arising out of the application or use of this document or any product described herein. This document is intended for skilled and technically trained engineering customers and users who design with Diodes' products. Diodes' products may be used to facilitate safety-related applications; however, in all instances customers and users are responsible for (a) selecting the appropriate Diodes products for their applications, (b) evaluating the suitability of Diodes' products for their intended applications, (c) ensuring their applications, which incorporate Diodes' products, comply the applicable legal and regulatory requirements as well as safety and functional-safety related standards, and (d) ensuring they design with appropriate safeguards (including testing, validation, quality control techniques, redundancy, malfunction prevention, and appropriate treatment for aging degradation) to minimize the risks associated with their applications.
- 3. Diodes assumes no liability for any application-related information, support, assistance or feedback that may be provided by Diodes from time to time. Any customer or user of this document or products described herein will assume all risks and liabilities associated with such use, and will hold Diodes and all companies whose products are represented herein or on Diodes' websites, harmless against all damages and liabilities.
- 4. Products described herein may be covered by one or more United States, international or foreign patents and pending patent applications. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks and trademark applications. Diodes does not convey any license under any of its intellectual property rights or the rights of any third parties (including third parties whose products and services may be described in this document or on Diodes' website) under this document.
- 5. Diodes' products are provided subject to Diodes' Standard Terms and Conditions of Sale (https://www.diodes.com/about/company/terms-and-conditions/terms-and-conditions-of-sales/) or other applicable terms. This document does not alter or expand the applicable warranties provided by Diodes. Diodes does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.
- 6. Diodes' products and technology may not be used for or incorporated into any products or systems whose manufacture, use or sale is prohibited under any applicable laws and regulations. Should customers or users use Diodes' products in contravention of any applicable laws or regulations, or for any unintended or unauthorized application, customers and users will (a) be solely responsible for any damages, losses or penalties arising in connection therewith or as a result thereof, and (b) indemnify and hold Diodes and its representatives and agents harmless against any and all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim relating to any noncompliance with the applicable laws and regulations, as well as any unintended or unauthorized application.
- 7. While efforts have been made to ensure the information contained in this document is accurate, complete and current, it may contain technical inaccuracies, omissions and typographical errors. Diodes does not warrant that information contained in this document is error-free and Diodes is under no obligation to update or otherwise correct this information. Notwithstanding the foregoing, Diodes reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes.
- 8. Any unauthorized copying, modification, distribution, transmission, display or other use of this document (or any portion hereof) is prohibited. Diodes assumes no responsibility for any losses incurred by the customers or users or any third parties arising from any such unauthorized use.
- 9. This Notice may be periodically updated with the most recent version available at https://www.diodes.com/about/company/terms-and-conditions/important-notice

DIODES is a trademark of Diodes Incorporated in the United States and other countries. The Diodes logo is a registered trademark of Diodes Incorporated in the United States and other countries. © 2022 Diodes Incorporated. All Rights Reserved.

www.diodes.com